Unit: mm

TOSHIBA Field Effect Transistor Silicon N-Channel MOS Type

SSM3K122TU

Power Management Switch Applications

- High-Speed Switching Applications
- AEC-Q101 qualified (Note 1)
- 1.5 V drive
 - Low ON-resistance: Ron = $304 \text{ m}\Omega \text{ (max)} (@VGS = 1.5 \text{ V})$
 - Ron = 211 m Ω (max) (@VGS = 1.8 V)
 - Ron = 161 m Ω (max) (@VGS = 2.5 V)

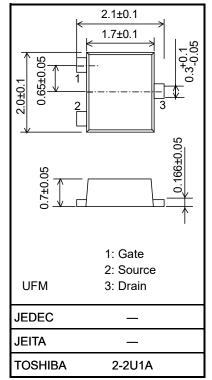
Ron = 123 mΩ (max) (@VGS = 4.0 V)

Note 1: For detail information, please contact our sales.

Absolute Maximum Ratings (Ta = 25°C)

Characteristics		Symbol	Rating	Unit	
Drain-Source voltage		V _{DSS}	20	V	
Gate-Source voltage		VGSS	± 10	V	
Drain current	DC	ID	2.0	А	
	Pulse	IDP	4.0		
Drain power dissipation		PD (Note 1)	800	mW	
		PD (Note 2)	500		
Channel temperature		T _{ch}	150	°C	
Storage temperature range		T _{stg}	–55 to 150	٥°	

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.



Weight: 6.6 mg (typ.)

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/ "Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

Note 1: Mounted on a ceramic board. (25.4 mm \times 25.4 mm \times 0.8 t, Cu Pad: 645 mm²) Note 2: Mounted on a FR4 board. (25.4 mm \times 25.4 mm \times 1.6 t, Cu Pad: 645 mm²)

Electrical Characteristics (Ta = 25°C)

Charact	eristics	Symbol	Test Condition	Min	Тур.	Мах	Unit
Drain-Source breakdown voltage	V (BR) DSS	$I_D = 1 \text{ mA}, \text{ V}_{GS} = 0 \text{ V}$	20		_	V	
	V (BR) DSX	$I_D = 1 \text{ mA}, V_{GS} = -10 \text{ V}$	12	—	_		
Drain cutoff curren	t	IDSS	V _{DS} = 20 V, V _{GS} = 0 V		—	1	μA
Gate leakage curre	ent	I _{GSS}	$V_{GS} = \pm 10 \text{ V}, V_{DS} = 0 \text{ V}$		—	±1	μA
Gate threshold vol	tage	Vth	$V_{DS} = 3 V, I_D = 1 mA$	0.35	—	1.0	V
Forward transfer a	dmittance	Yfs	V _{DS} = 3 V, I _D = 1.0 A (Note 3)	2.6	5.2	_	S
Drain-Source ON-resistance	Rds (ON)	$I_D = 1.0 \text{ A}, V_{GS} = 4.0 \text{ V}$ (Note 3)		87	123	- mΩ	
		I _D = 1.0 A, V _{GS} = 2.5 V (Note 3)		112	161		
		I _D = 0.5 A, V _{GS} = 1.8 V (Note 3)		147	211		
		$I_D = 0.3 \text{ A}, V_{GS} = 1.5 \text{ V}$ (Note 3)		182	304		
Input capacitance		Ciss			195		pF
Output capacitance		Coss	V _{DS} = 10 V, V _{GS} = 0 V, f = 1 MHz		35		
Reverse transfer capacitance		Crss	1		29	_	
Total Gate Charge G		Qg			3.4	_	nC
Gate-Source Charge		Qgs	V _{DS} = 10 V, I _D = 2.0 A, V _{GS} = 4 V		2.3	_	
Gate-Drain Charge		Q _{gd}	1		1.1	_	
Switching time	Turn-on time	t _{on}	$V_{DD} = 10 \text{ V}, \text{ I}_{D} = 0.5 \text{ A},$		8.0	_	ns
	Turn-off time	toff	VGS = 0 to 2.5 V, RG = 4.7 Ω		9.0	_	
Drain-Source forwa	ard voltage	VDSF	$I_D = -2.0 \text{ A}, V_{GS} = 0 \text{ V}$ (Note 3)	—	-0.85	-1.2	V

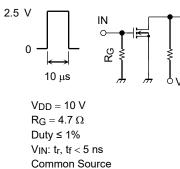
Note 3: Pulse test

Switching Time Test Circuit

(a) Test Circuit

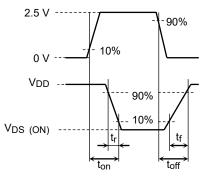
(b) VIN

OUT



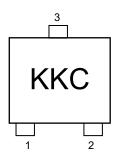
Ta = 25°C

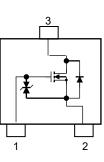




Marking

Equivalent Circuit (top view)





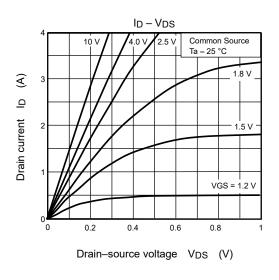
Notice on Usage

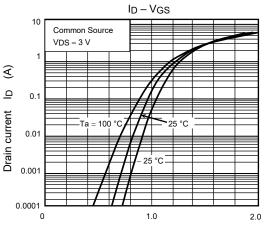
Vth can be expressed as the voltage between gate and source when the low operating current value is ID = 1 mA for this product. For normal switching operation, VGS (on) requires a higher voltage than Vth, and VGS (off) requires a lower voltage than Vth. (The relationship can be established as follows: VGS (off) < Vth < VGS (on).)

Take this into consideration when using the device.

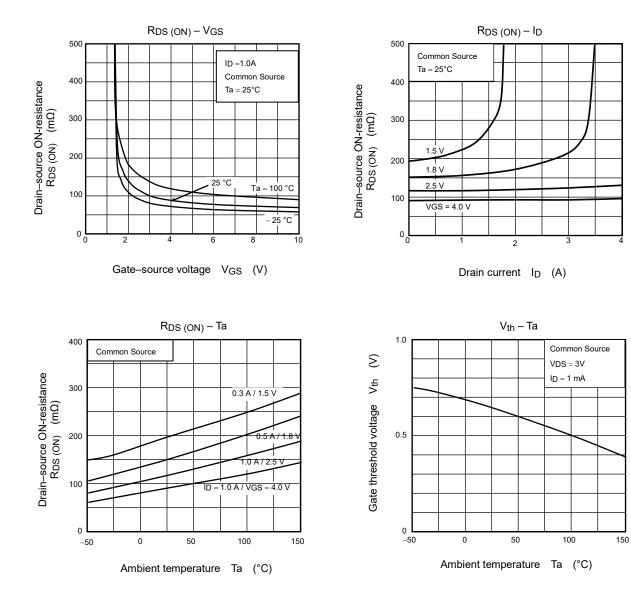
Handling Precaution

When handling individual devices that are not yet mounted on a circuit board, make sure that the environment is protected against electrostatic discharge. Operators should wear antistatic clothing, and containers and other objects that come into direct contact with devices should be made of antistatic materials.

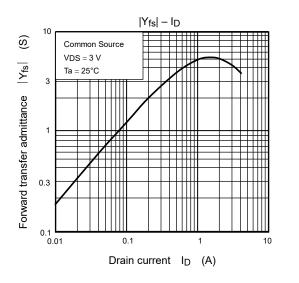


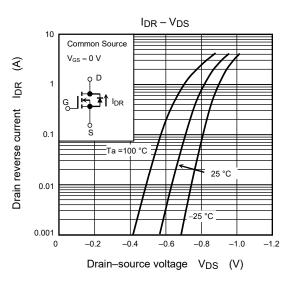


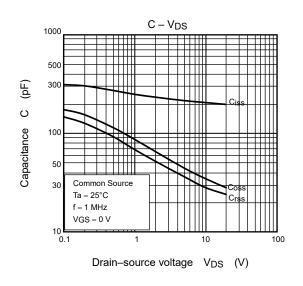
Gate-source voltage VGS (V)

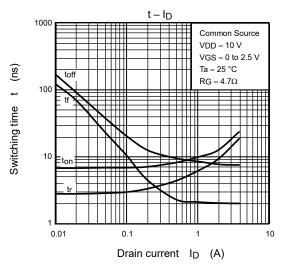


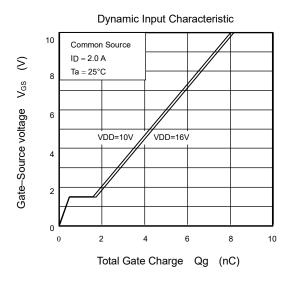
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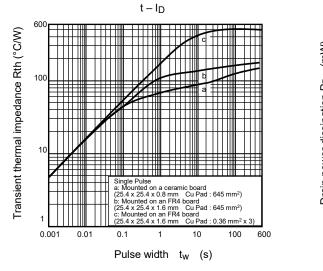


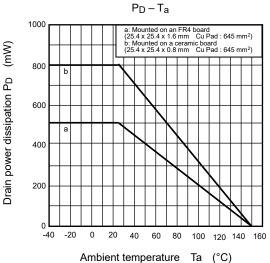




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